

## Silicon PNP Power Transistors

## BDX66B

## DESCRIPTION

- With TO-3 package
- High current
- DARLINGTON

## APPLICATIONS

- Designed for power amplification and switching applications.

## PINNING (See Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

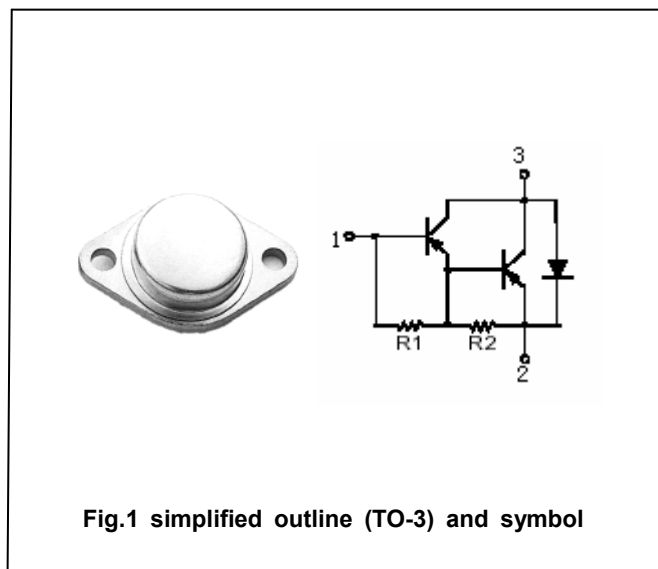


Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings( $T_a=25^\circ\text{C}$ )

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$V_{CBO}$	Collector-base voltage	Open emitter	-100	V
$V_{CEO}$	Collector-emitter voltage	Open base	-100	V
$V_{EBO}$	Emitter-base voltage	Open collector	-5	V
$I_C$	Collector current		-16	A
$I_{CM}$	Collector current(peak)		-20	A
$I_B$	Base current		-0.25	A
$P_T$	Total power dissipation	$T_C=25^\circ\text{C}$	150	W
$T_j$	Junction temperature		-55~200	$^\circ\text{C}$
$T_{stg}$	Storage temperature		-55~200	$^\circ\text{C}$

## THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal resistance from junction to case	1.17	$^\circ\text{C}/\text{W}$

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## CHARACTERISTICS

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 $T_j = 25^\circ\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEQ(SUS)}$	Collector-emitter sustaining voltage	$I_C = -0.1\text{A}$ ; $I_B = 0$ ; $L = 25\text{mH}$	-100			V
$V_{CEsat}$	Collector-emitter saturation voltage	$I_C = -10\text{A}$ ; $I_B = -40\text{mA}$			-2	V
$I_{CBO}$	Collector cut-off current	$V_{CB} = -60\text{V}$ ; $I_E = 0$ $T_C = 150^\circ\text{C}$			-1 -5	mA
$I_{CEO}$	Collector cut-off current	$V_{CE} = -50\text{V}$ ; $I_B = 0$			-3	mA
$I_{EBO}$	Emitter cut-off current	$V_{EB} = -5\text{V}$ ; $I_C = 0$			-5	mA

## Switching times

$t_{on}$	Turn-on time	$I_C = -10\text{A}$ ; $I_{B1} = -I_{B2} = 0.04\text{A}$ $V_{CC} = 12\text{V}$ ;		1.0		$\mu\text{s}$
$t_{off}$	Turn-off time			3.5		$\mu\text{s}$

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## PACKAGE OUTLINE

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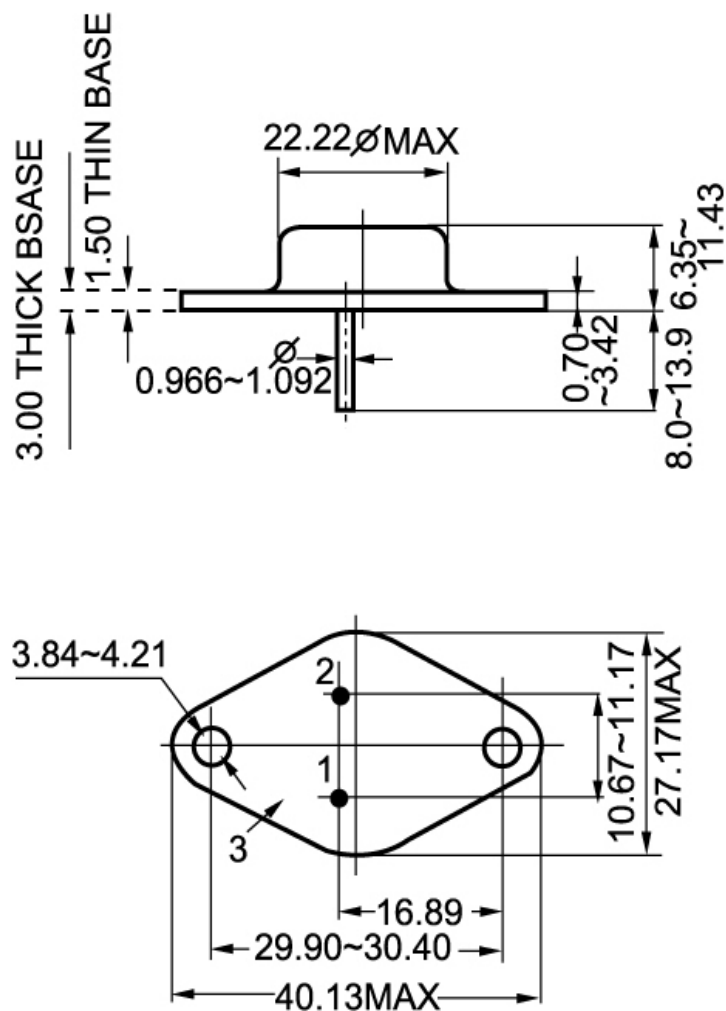


Fig.2 Outline dimensions